

Serial No. 10/715,376
Docket No. YOR920030332US1

AMENDMENTS TO THE CLAIMS:

1. (Original) A spin-current switched magnetic memory element, comprising:
a plurality of magnetic layers, at least one of said plurality of magnetic layers having a perpendicular magnetic anisotropy component and comprising a current-switchable magnetic moment; and
at least one barrier layer formed adjacent to said plurality of magnetic layers.
2. (Original) The spin-current switched magnetic memory element according to claim 1, wherein said plurality of magnetic layers comprises at least one composite layer.
3. (Original) The spin-current switched magnetic memory element according to claim 2, wherein said at least one composite layer comprises a platinum layer and a cobalt layer.
4. (Original) The spin-current switched magnetic memory element according to claim 2, wherein said at least one composite layer comprises a gold layer and a cobalt layer.
5. (Original) The spin-current switched magnetic memory element according to claim 2, wherein said at least one composite layer comprises a nickel layer and a copper layer.
6. (Original) The spin-current switched magnetic memory element according to claim 2, wherein said perpendicular magnetic anisotropy component is formed at an interface between a magnetic layer and non-magnetic layer of said at least one composite layer.
7. (Original) The spin-current switched magnetic memory element according to claim 2, wherein said perpendicular magnetic anisotropy component comprises a bulk perpendicular magnetic anisotropy component which is formed in a magnetic layer of the said at least one composite layer.

Serial No. 10/715,376

Docket No. YOR920030332US1

8. (Original) The spin-current switched magnetic memory element according to claim 1, further comprising:
- first and second leads; and
 - a pillar formed between said first and second leads, said pillar including said at least one barrier layer and at least one magnetic layer of said plurality of magnetic layers.
9. (Currently amended) The spin-current switched magnetic memory element according to claim 8 9, wherein said at least one magnetic layer included in said pillar comprises said current-switchable magnetic moment.
10. (Currently amended) The spin-current switched magnetic memory element according to claim 9 10, wherein said magnetic moment of said at least one magnetic layer included in said pillar is switchable by an electrical current having a density of no more than about 10^6 A/cm².
11. (Currently amended) The spin-current switched magnetic memory element according to claim 8 9, wherein said barrier layer preserves spin information for an electric current injected into said pillar and provides a resistance to said current.
12. (Currently amended) The spin-current switched magnetic memory element according to claim 8 9, wherein at least one of said first and second leads includes a magnetic layer of said plurality of magnetic layers.
13. (Original) The spin-current switched magnetic memory element according to claim 1, wherein said plurality of magnetic layers comprises an upper magnetic layer and a lower magnetic layer, said at least one barrier layer being formed between said upper and lower magnetic layers.
14. (Currently amended) The spin-current switched magnetic memory element according to claim 13 14, wherein said upper magnetic layer comprises one of a platinum layer formed on a cobalt layer, and a gold layer formed on a cobalt layer.

Serial No. 10/715,376

Docket No. YOR920030332US1

15. (Currently amended) The spin-current switched magnetic memory element according to claim 13 14, wherein said lower magnetic layer comprises one of a cobalt layer formed on a platinum layer, a cobalt layer formed on a gold layer, and a nickel layer formed on a copper layer.

16. (Currently amended) The spin-current switched magnetic memory element according to claim 1, wherein said perpendicular magnetic ~~anisotropy~~ anisotropy has a magnitude sufficient to at least substantially offset an easy-plane demagnetization effect, such that a magnetic moment of one of said upper and lower magnetic layers is either resting out of the film plane or can be rotated out of the film plane under spin current excitation.

17. (Original) The spin-current switched magnetic memory element according to claim 1, wherein said at least one barrier layer comprises a plurality of barrier layers which are alternately formed with said plurality of magnetic layers.

18. (Currently amended) The spin-current switched magnetic memory element according to claim 8 9, wherein said pillar comprises a lithographed pillar having a diameter of less than about 100 nm, and having an oblong-shaped cross-section.

19. (Original) The spin-current switched magnetic memory element according to claim 1, wherein said at least one barrier layer comprises a tunneling barrier layer.

20. (Original) The spin-current switched magnetic memory element according to claim 1, wherein said at least one barrier layer comprises at least one of an aluminum oxide layer, a magnesium oxide layer, a doped semiconductor layer, a non-magnetic metal layer and a SrTiO₃ layer.

21. (Currently amended) The spin-current switched magnetic memory element according to claim 13 14, wherein said lower magnetic layer comprises a first nickel layer formed on a first copper layer, and said upper magnetic layer comprises a second copper layer formed on a second nickel layer.

Serial No. 10/715,376
Docket No. YOR920030332US1

22. (Currently amended) The spin-current switched magnetic memory element according to claim 21 ~~22~~, wherein said second nickel layer has a thickness which is different than a thickness of said first nickel layer, and has a magnetic moment which is perpendicular to a film plane, and wherein one of said first and second nickel layers represents an information storage state and has a magnetic moment which is rotatable under an influence of a write current, and the other provides a reference magnetic direction which is not rotatable under said influence of said write current.

23. (Currently amended) The spin-current switched magnetic memory element according to claim 13 ~~14~~, wherein said lower magnetic layer comprises a first cobalt layer formed on a first platinum layer, and said upper magnetic layer comprises a second platinum layer formed on a second cobalt layer.

24. (Currently amended) The spin-current switched magnetic memory element according to claim 13 ~~14~~, wherein said pillar has an electrical resistance which depends on a magnetization direction of said lower magnetic layer with respect to a magnetization direction of said upper layer.

25. (Currently amended) The spin-current switched magnetic memory element according to claim 13 ~~14~~, wherein said pillar comprises a magnetic tunneling junction across said barrier layer between said upper and lower magnetic layers.

26. (Original) A spin-current switched magnetic memory element, comprising:
first and second leads;
a pillar formed between said first and second leads,
a plurality of magnetic layers, at least one of said plurality of magnetic layers having a perpendicular magnetic anisotropy component and comprising a current-switchable magnetic moment; and
at least one barrier layer formed in said pillar adjacent to said plurality of magnetic layers.

Serial No. 10/715,376
Docket No. YOR920030332US1

27. (Currently amended) A magnetic random access memory (MRAM) array comprising a plurality of magnetic spin-current switched magnetic memory elements according to claim 26 27.

28. (Original) A method of fabricating a spin-current switched magnetic memory element, said method comprising:

providing a wafer having a bottom electrode;

forming a plurality of layers, such that interfaces between said plurality of layers are formed in situ, said plurality of layers comprising:

a plurality of magnetic layers, at least one of said plurality of magnetic layers having a perpendicular magnetic anisotropy component and comprising a current-switchable magnetic moment; and

at least one barrier layer formed adjacent to said plurality of magnetic layers;

lithographically defining a pillar structure from said plurality of layers; and

forming a top electrode on said pillar structure.

29. (Currently amended) The method according to claim 28 29, wherein said at least one barrier layer comprises a plurality of barrier layers which are alternately formed with said plurality of magnetic layers.

30. (New) The spin-current switched magnetic memory element according to claim 1, wherein said perpendicular magnetic anisotropy at least substantially counters an easy-plane demagnetization effect in said plurality of magnetic layers.

31. (New) The spin-current switched magnetic memory element according to claim 1, wherein said at least one barrier layer comprises at least one of a magnesium oxide layer, a doped semiconductor layer, a non-magnetic metal layer and a SrTiO₃ layer.

32. (New) The spin-current switched magnetic memory element according to claim 1, wherein said magnetic moment is switchable by using only current and without using heat or a

Serial No. 10/715,376
Docket No. YOR920030332US1

magnetic field.

33. (New) The spin-current switched magnetic memory element according to claim 1, wherein said perpendicular magnetic anisotropy is induced at one of the interface away from the tunnel barrier and a location where a useful spin-density accumulates, allowing a magnetically switchable layer in said plurality of magnetic layers to be a significant body for spin-angular momentum absorption.

34. (New) The spin-current switched magnetic memory element according to claim 1, wherein said plurality of magnetic layer comprises a switching layer which alone comprises at least a perpendicular anisotropy component, and
wherein a rest-direction of the magnetization of the plurality of magnetic layers do not become perpendicular to the film plane.